



Plastic-Encapsulate Transistors

DUAL TRANSISTOR (NPN+NPN)

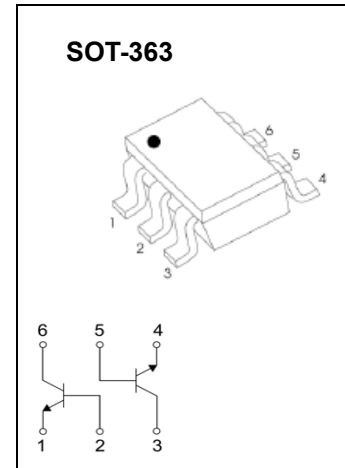
FEATURES

- Epitaxial planar die construction
- Ideal for low power amplification and switching

MARKING:K6N

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	0.2	A
P _C	Collector Power Dissipation	0.2	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =10μA, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10μA, I _C =0	5			V
Collector cut-off current	I _{CB0}	V _{CB} =30V, I _E =0			0.05	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			0.05	μA
Collector cut-off current	I _{CEX}	V _{CE} =30V, V _{BE(off)} =3V			0.05	μA
DC current gain	h _{FE(1)}	V _{CE} =1V, I _C =0.1mA	40			
	h _{FE(2)}	V _{CE} =1V, I _C =1mA	70			
	h _{FE(3)}	V _{CE} =1V, I _C =10mA	100		300	
	h _{FE(4)}	V _{CE} =1V, I _C =50mA	60			
	h _{FE(5)}	V _{CE} =1V, I _C =100mA	30			
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =10mA, I _B =1mA			0.2	V
	V _{CE(sat)2}	I _C =50mA, I _B =5mA			0.3	V
Base-emitter saturation voltage	V _{BE(sat)1}	I _C =10mA, I _B =1mA	0.65		0.85	V
	V _{BE(sat)2}	I _C =50mA, I _B =5mA			0.95	V
Transition frequency	f _T	V _{CE} =20V, I _C =10mA, f=100MHz	300			MHz
Collector output capacitance	C _{ob}	V _{CB} =5V, I _E =0, f=1MHz			4	pF
Noise figure	NF	V _{CE} =5V, I _C =0.1mA, f=1kHz, R _S =1KΩ			5	dB
Delay time	t _d	V _{CC} =3V, V _{BE(off)} =-0.5V			35	nS
Rise time	t _r	I _C =10mA, I _{B1} =-I _{B2} =1mA			35	nS
Storage time	t _s	V _{CC} =3V, I _C =10mA			200	nS
Fall time	t _f	I _{B1} =-I _{B2} =1mA			50	nS

TYPICAL TRANSIENT CHARACTERISTICS

— $T_J = 25^\circ\text{C}$
- - $T_J = 125^\circ\text{C}$

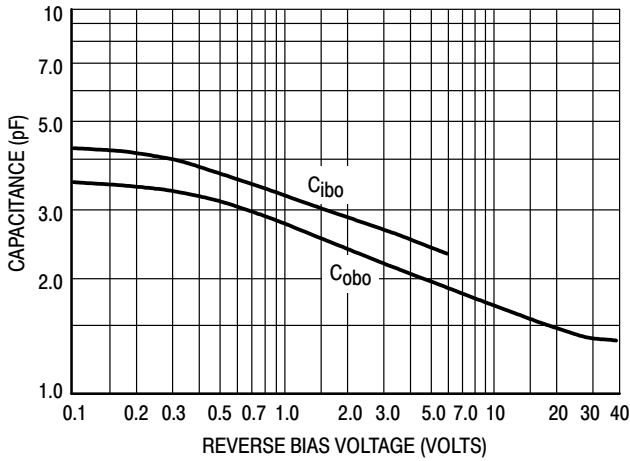


Figure 3. Capacitance

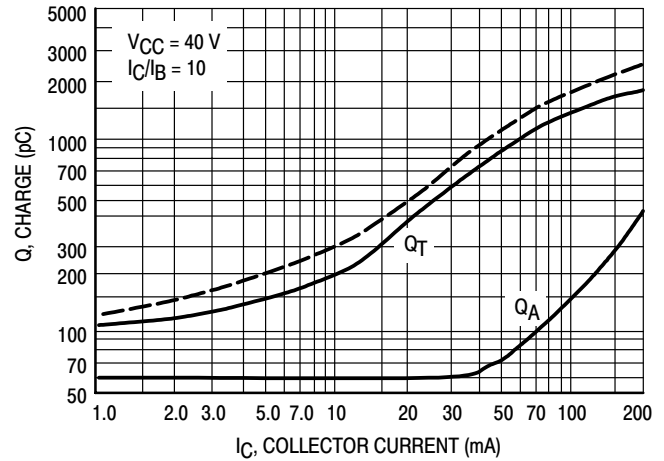


Figure 4. Charge Data

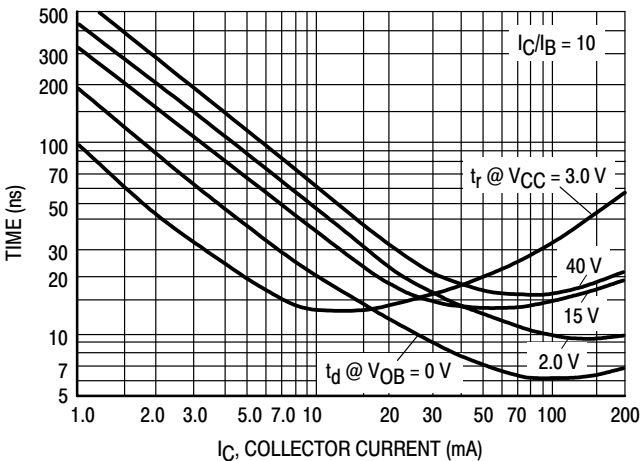


Figure 5. Turn-On Time

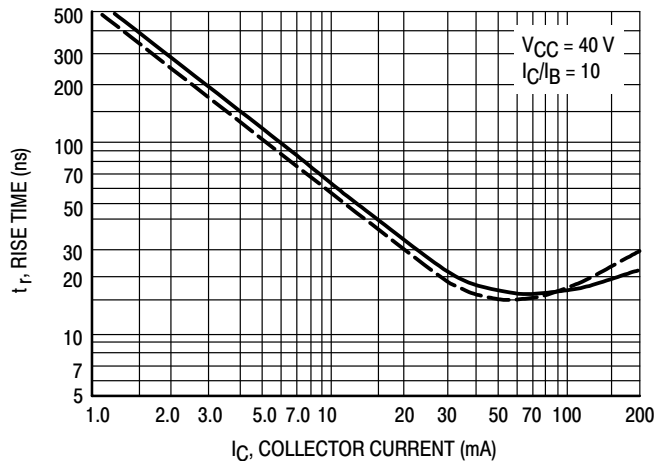


Figure 6. Rise Time

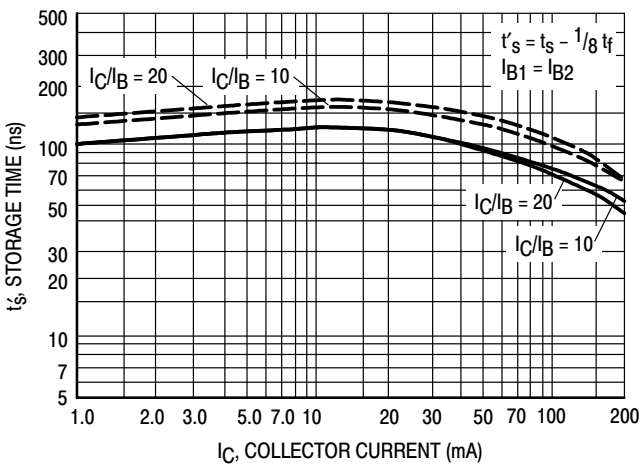


Figure 7. Storage Time

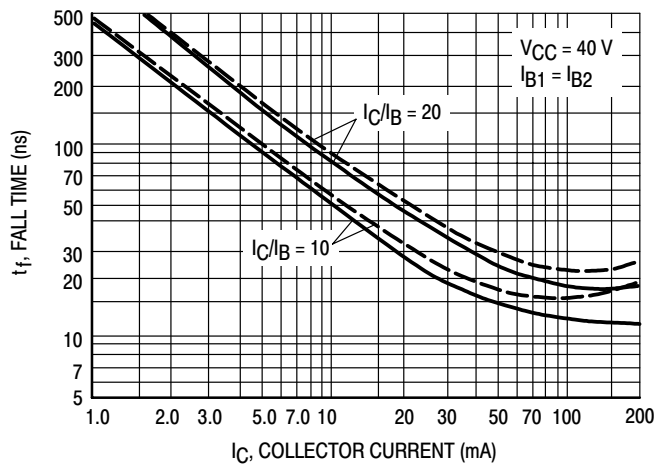


Figure 8. Fall Time



TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS
NOISE FIGURE VARIATIONS

(V_{CE} = 5.0 Vdc, T_A = 25°C, Bandwidth = 1.0 Hz)

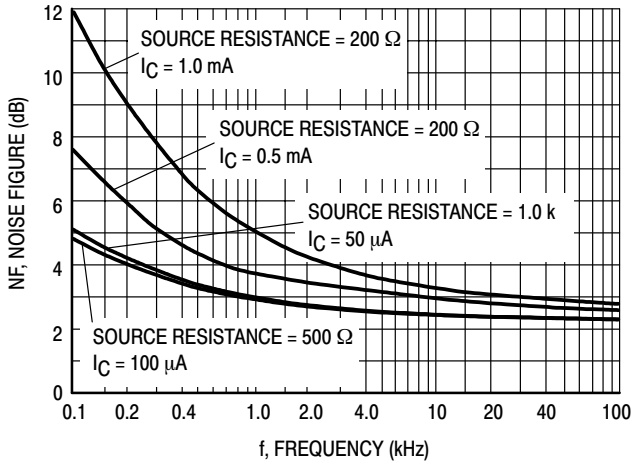


Figure 9. Noise Figure

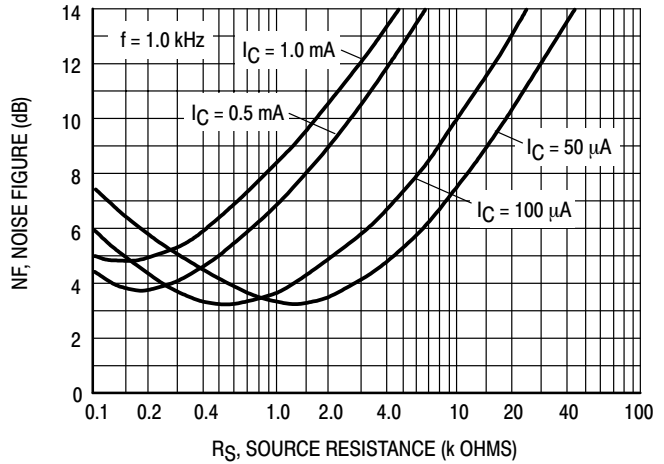


Figure 10. Noise Figure

h PARAMETERS

(V_{CE} = 10 Vdc, f = 1.0 kHz, T_A = 25°C)

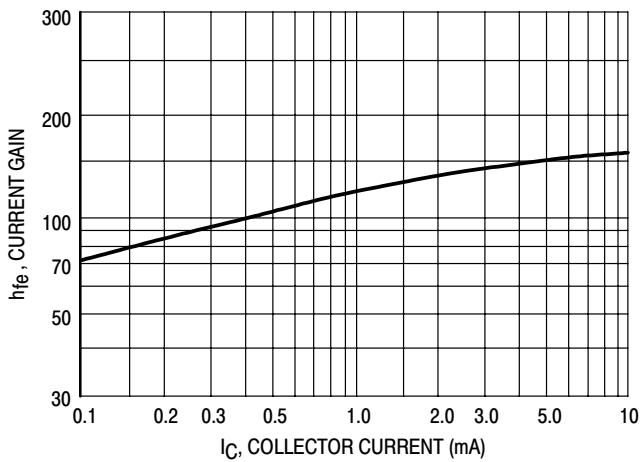


Figure 11. Current Gain

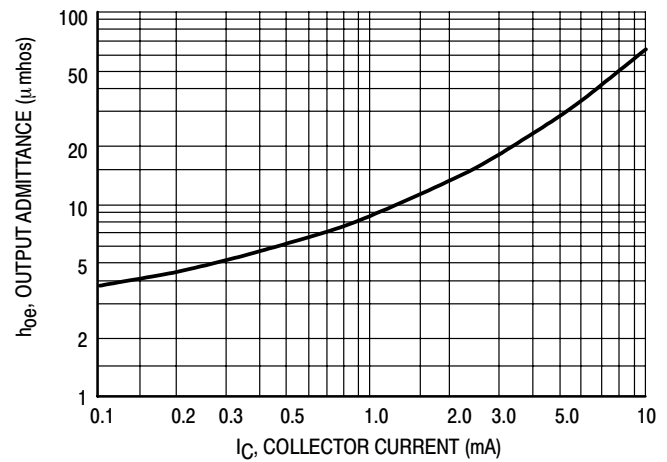


Figure 12. Output Admittance

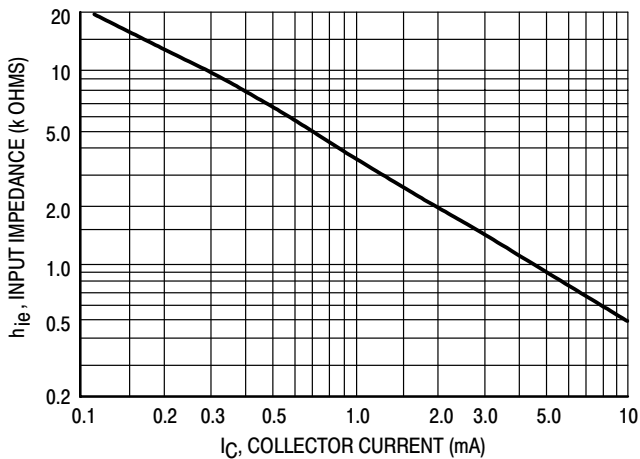


Figure 13. Input Impedance

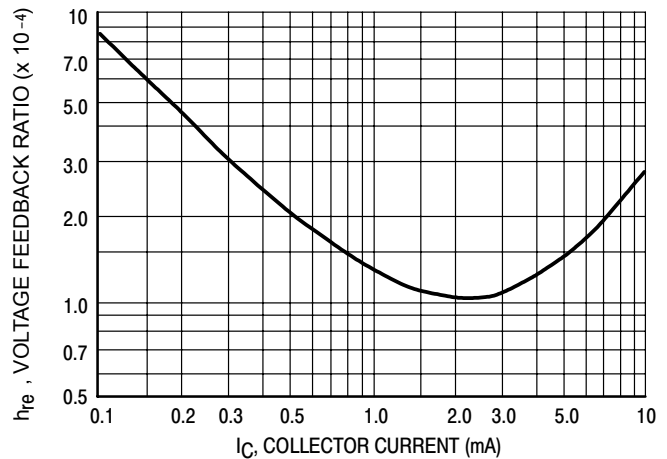


Figure 14. Voltage Feedback Ratio



TYPICAL STATIC CHARACTERISTICS

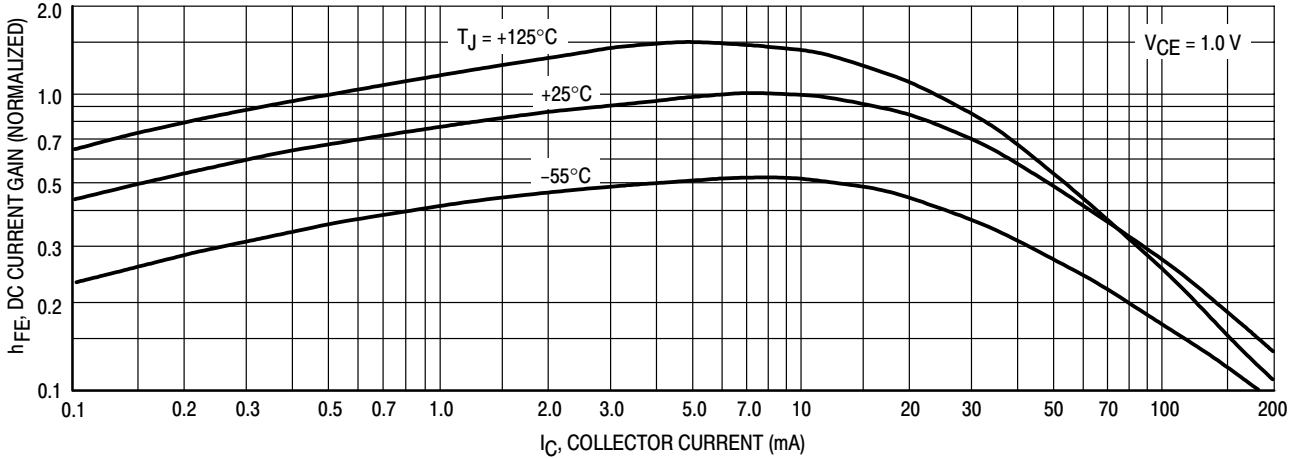


Figure 15. DC Current Gain

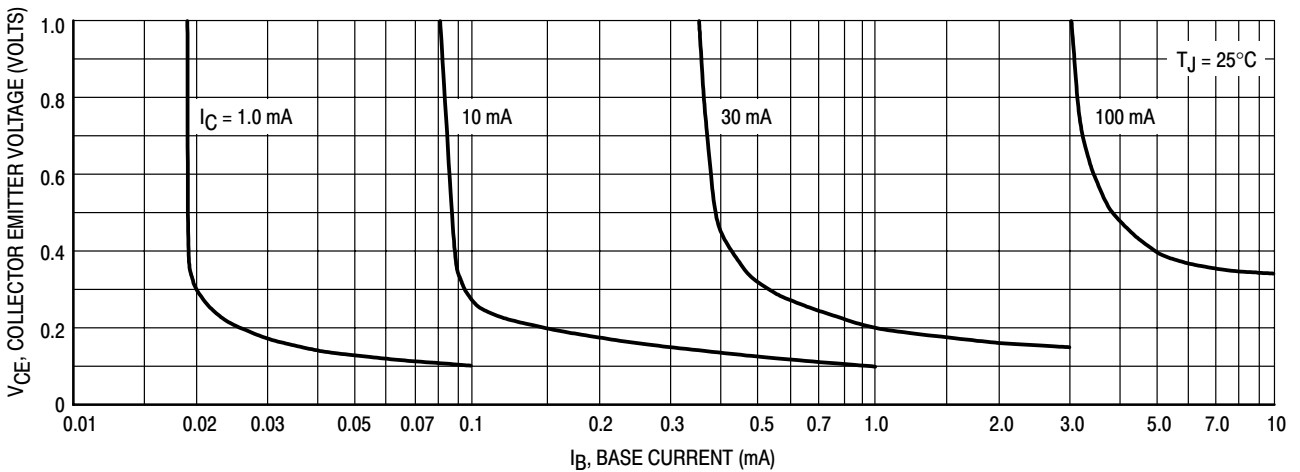


Figure 16. Collector Saturation Region

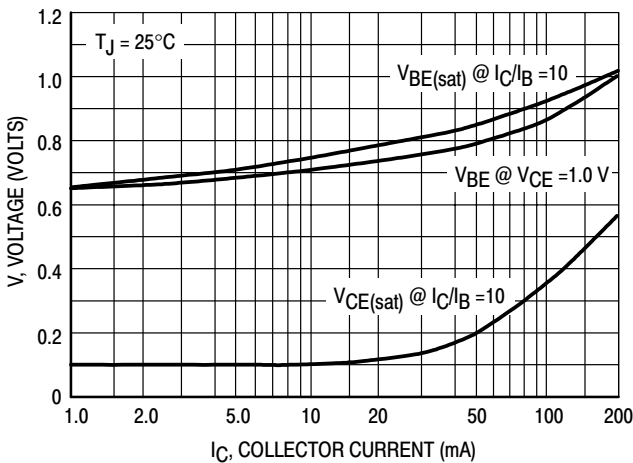


Figure 17. "ON" Voltages

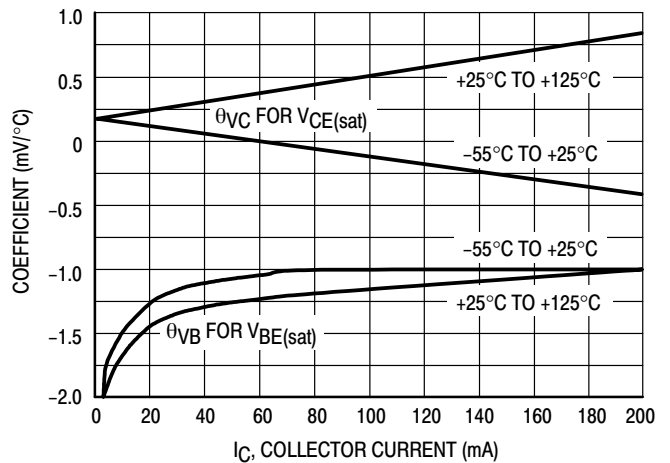
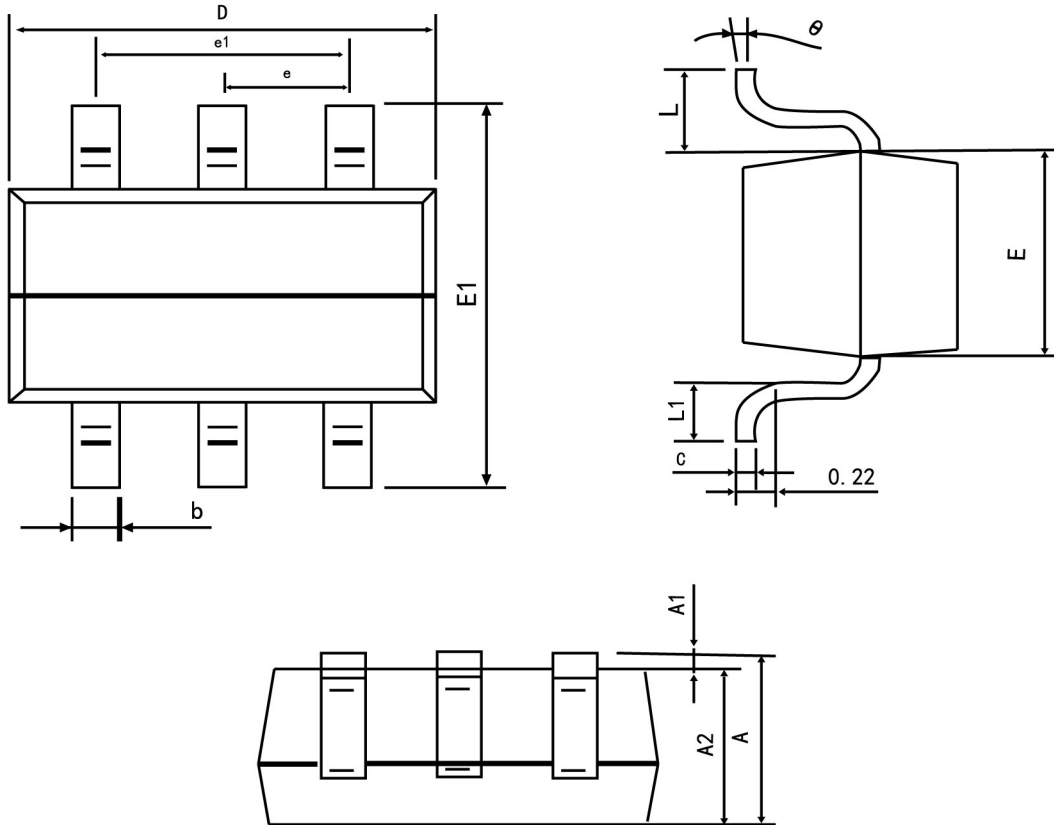


Figure 18. Temperature Coefficients



SOT-363-Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°